

FEATURES

Complimentary to S9013
Collector current: $I_C=0.5A$

MARKING: 2T1

SOT-23

1. BASE
2. EMITTER
3. COLLECTOR



MAXIMUM RATINGS (TA=25°C unless otherwise noted)

Symbol (符号)	Parameter (参数名称)	Value (额定值)	Units (单位)
VCBO	Collector-Base Voltage (集电极-基极电压)	-40	V
VCEO	Collector-Emitter Voltage (集电极-发射极电压)	-25	V
VEBO	Emitter-Base Voltage (发射极-基极电压)	-5	V
IC	Collector Current -Continuous (集电极电流)	-0.5	A
PC	Collector Power Dissipation (耗散功率)	0.3	W
Tj	Junction Temperature (结温)	150	°C
Tstg	Storage Temperature (储存温度)	-55-150	°C

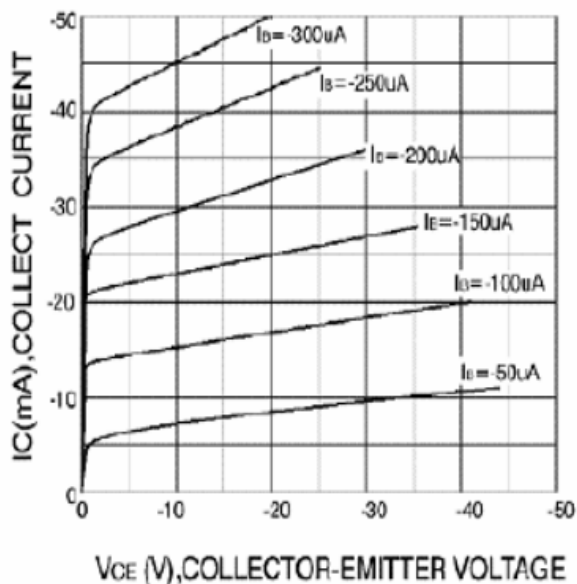
ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter (参数名称)	Symbol (符号)	Test conditions (测试条件)	MIN (最小值)	TYP (典型值)	MAX (最大值)	UNIT (单位)
Collector-base breakdown voltage 集电极-基极击穿电压	V(BR)CBO	$I_C = -100\mu A$, $I_E = 0$	-40			V
Collector-emitter breakdown voltage 集电极-发射极击穿电压	V(BR)CEO	$I_C = -1mA$, $I_B = 0$	-25			V
Emitter-base breakdown voltage 发射极-基极击穿电压	V(BR)EBO	$I_E = -100\mu A$, $I_C = 0$	-5			V
Collector cut-off current 集电极-基极截止电流	ICBO	$V_{CB} = -30V$, $I_E = 0$			-1	μA
Collector cut-off current 集电极-发射极截止电流	ICEO	$V_{CE} = -25V$, $I_B = 0$			-10	μA
Emitter cut-off current 发射极-基极截止电流	IEBO	$V_{EB} = -5V$, $I_C = 0$			-1	μA
DC current gain 直流电流增益	hFE	$V_{CE} = -1V$, $I_C = -50mA$	80		400	
Collector-emitter saturation voltage 集电极-发射极饱和压降	VCE(sat)	$I_C = -500mA$, $I_B = -50mA$			-0.5	V
Base-emitter saturation voltage 发射极-基极饱和压降	VBE(sat)	$I_C = -500mA$, $I_B = -50mA$			-1.2	V

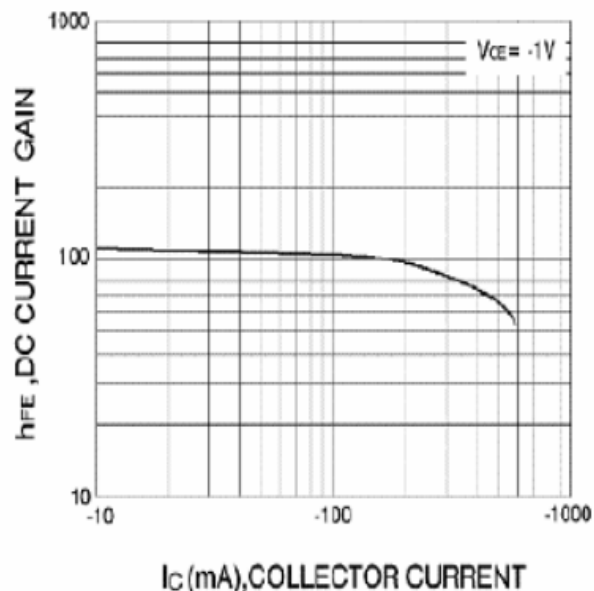
CLASSIFICATION OF hFE

Range	80-100	100-200	200-400	400-600
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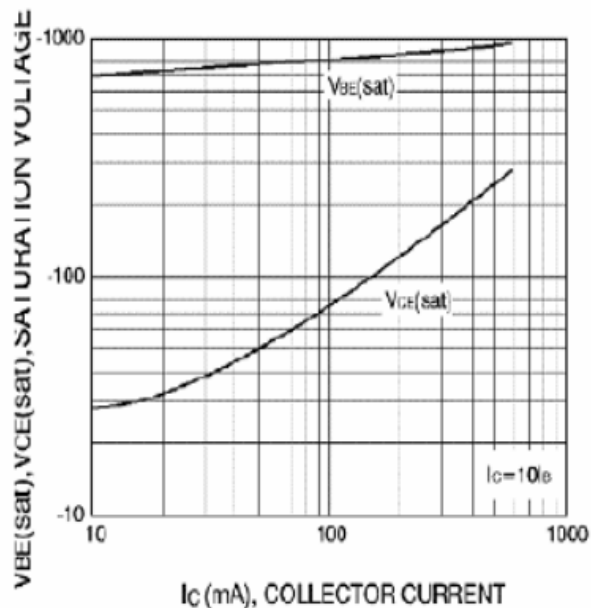
Typical Characteristics



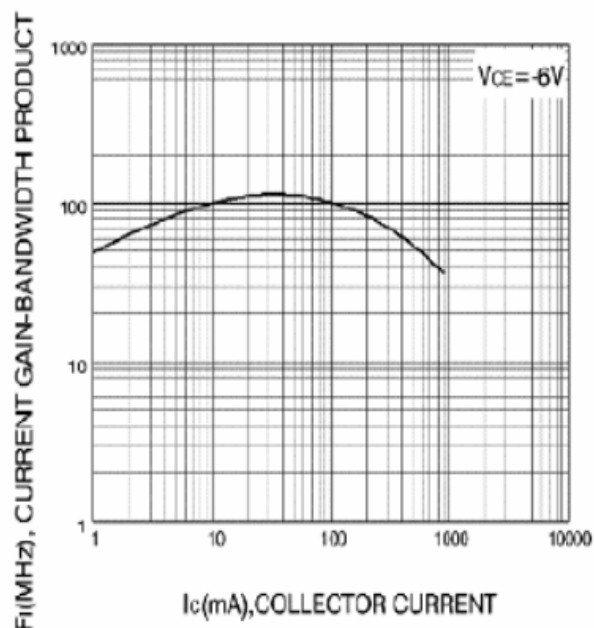
Static Characteristic



DC current Gain



Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage



Current Gain Bandwidth Product